

EMF5XV6T5

Preferred Devices

Power Management, Dual Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These are Pb-Free Devices

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
--------	--------	-------	------

Q₁ (T_A = 25°C unless otherwise noted, common for Q₁ and Q₂)

Collector-Base Voltage	V _{CB0}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	I _C	100	mAdc
Electrostatic Discharge	ESD	HBM Class 1 MM Class B	

Q₂ (T_A = 25°C)

Collector-Emitter Voltage	V _{CEO}	-12	Vdc
Collector-Base Voltage	V _{CB0}	-15	Vdc
Emitter-Base Voltage	V _{EBO}	-6.0	Vdc
Collector Current – Peak – Continuous	I _C	-1.0 (Note 1) -0.5	Adc
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	357 (Note 2) 2.9 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	350 (Note 2)	°C/W
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D	500 (Note 2) 4.0 (Note 2)	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA}	250 (Note 2)	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

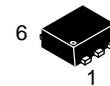
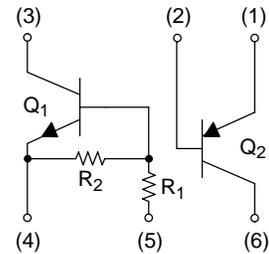
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Single pulse 1.0 ms.
2. FR-4 @ Minimum Pad.



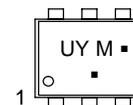
ON Semiconductor®

<http://onsemi.com>



SOT-563
CASE 463A
PLASTIC

MARKING DIAGRAM



UY = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
EMF5XV6T5	SOT-563 (Pb-Free)	8000/Tape & Reel
EMF5XV6T5G	SOT-563 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

EMF5XV6T5

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, common for Q_1 and Q_2)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

Q₁

OFF CHARACTERISTICS

Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}, I_E = 0$)	I_{CBO}	-	-	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}, I_B = 0$)	I_{CEO}	-	-	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}, I_C = 0$)	I_{EBO}	-	-	0.1	mAdc
Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}, I_E = 0$)	$V_{(BR)CBO}$	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 2.0\text{ mA}, I_B = 0$)	$V_{(BR)CEO}$	50	-	-	Vdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($V_{CE} = 10\text{ V}, I_C = 5.0\text{ mA}$)	h_{FE}	80	140	-	
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}, I_B = 0.3\text{ mA}$)	$V_{CE(sat)}$	-	-	0.25	Vdc
Output Voltage (on) ($V_{CC} = 5.0\text{ V}, V_B = 3.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OL}	-	-	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}, V_B = 0.5\text{ V}, R_L = 1.0\text{ k}\Omega$)	V_{OH}	4.9	-	-	Vdc
Input Resistor	R1	32.9	47	61.1	k Ω
Resistor Ratio	R1/R2	0.8	1.0	1.2	

Q₂

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = -10\text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	-12	-	-	Vdc
Collector-Base Breakdown Voltage ($I_C = -0.1\text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	-15	-	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = -0.1\text{ mAdc}, I_C = 0$)	$V_{(BR)EBO}$	-6.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = -15\text{ Vdc}, I_E = 0$)	I_{CBO}	-	-	-0.1	μAdc
Emitter Cutoff Current ($V_{EB} = -6.0\text{ Vdc}$)	I_{EBO}	-	-	-0.1	μAdc

ON CHARACTERISTICS

DC Current Gain (Note 4) ($I_C = -10\text{ mA}, V_{CE} = -2.0\text{ V}$)	h_{FE}	270	-	680	
Collector-Emitter Saturation Voltage (Note 4) ($I_C = -200\text{ mA}, I_B = -10\text{ mA}$)	$V_{CE(sat)}$	-	-	-250	mV
Base-Emitter Saturation Voltage (Note 4) ($I_C = -150\text{ mA}, I_B = -20\text{ mA}$)	$V_{BE(sat)}$	-	-0.81	-0.90	V
Base-Emitter Turn-on Voltage (Note 4) ($I_C = -150\text{ mA}, V_{CE} = -3.0\text{ V}$)	$V_{BE(on)}$	-	-0.81	-0.875	V
Input Capacitance ($V_{EB} = 0\text{ V}, f = 1.0\text{ MHz}$)	C_{ibo}	-	52	-	pF
Output Capacitance ($V_{CB} = 0\text{ V}, f = 1.0\text{ MHz}$)	C_{obo}	-	30	-	pF
Turn-On Time ($I_{B1} = -50\text{ mA}, I_C = -500\text{ mA}, R_L = 3.0\text{ }\Omega$)	t_{on}	-	50	-	ns
Turn-Off Time ($I_{B1} = I_{B2} = -50\text{ mA}, I_C = -500\text{ mA}, R_L = 3.0\text{ }\Omega$)	t_{off}	-	80	-	ns

3. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

4. Pulsed Condition: Pulse Width = 300 μsec , Duty Cycle \leq 2%.

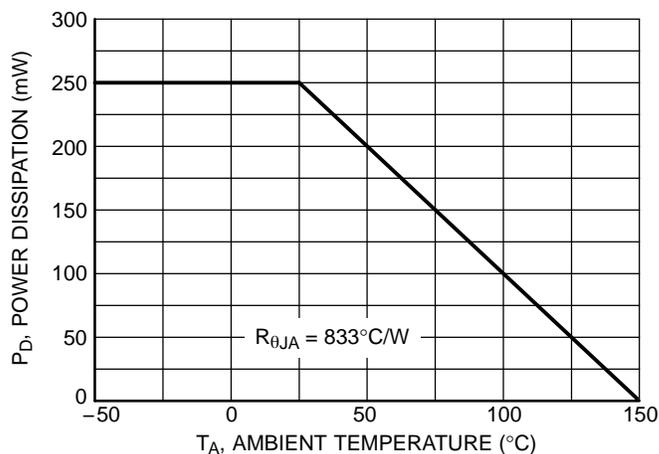


Figure 1. Derating Curve

EMF5XV6T5

TYPICAL ELECTRICAL CHARACTERISTICS FOR Q1

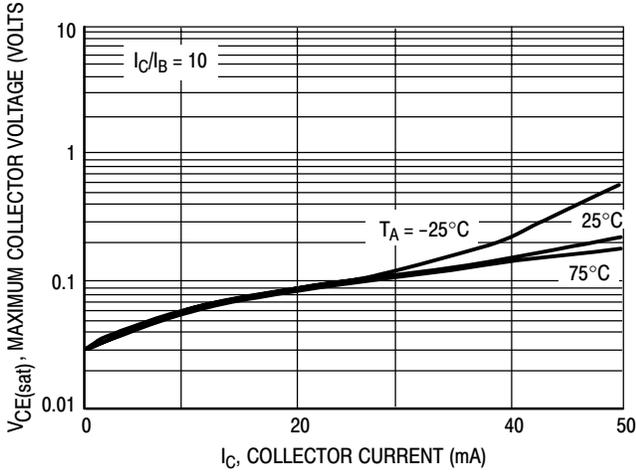


Figure 2. $V_{CE(sat)}$ versus I_C

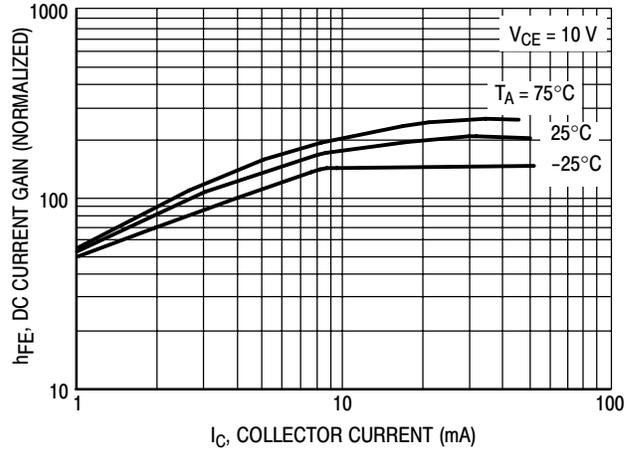


Figure 3. DC Current Gain

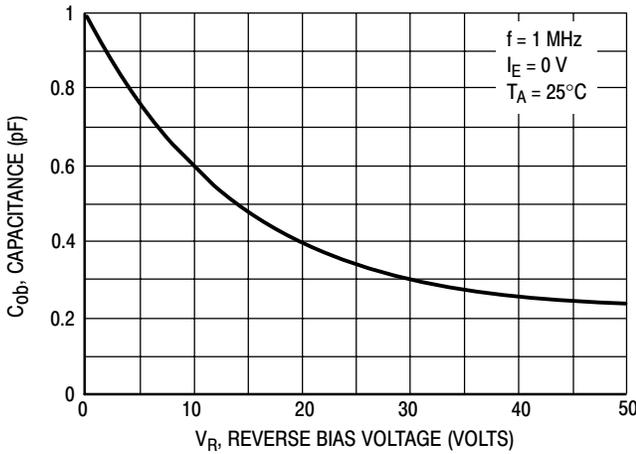


Figure 4. Output Capacitance

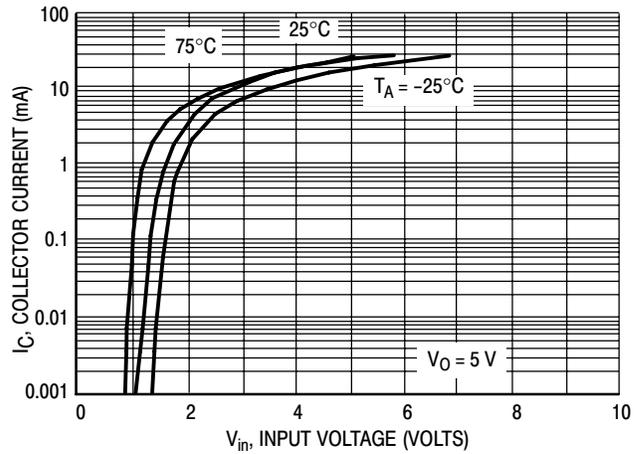


Figure 5. Output Current versus Input Voltage

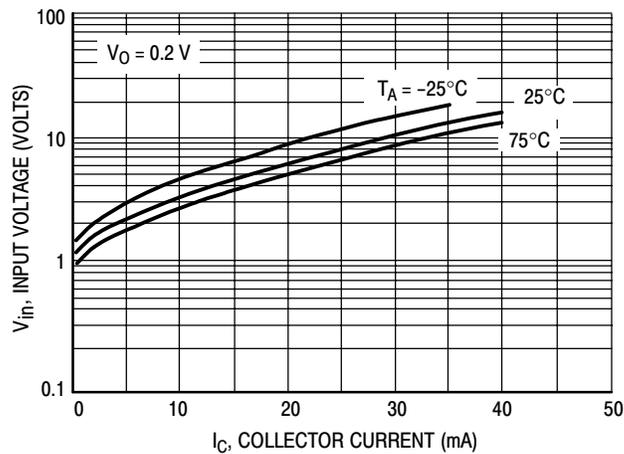


Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS FOR Q2

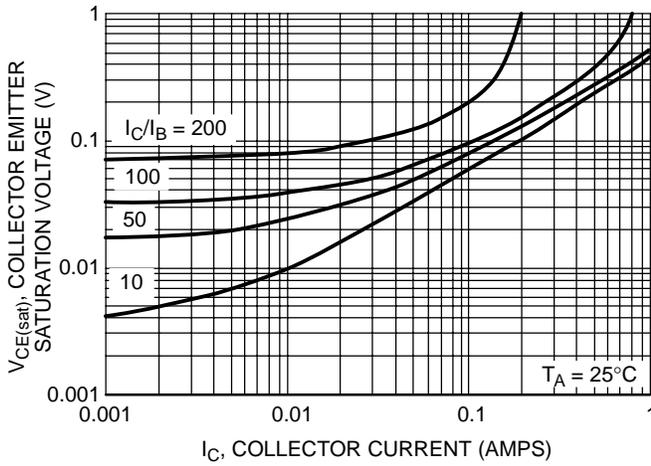


Figure 7. Collector Emitter Saturation Voltage vs. Collector Current

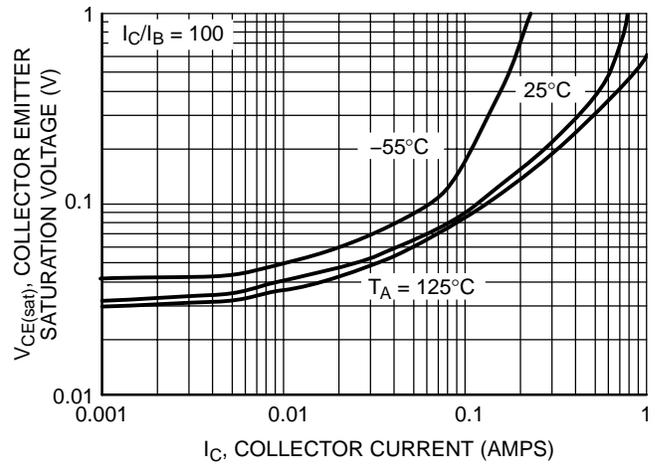


Figure 8. Collector Emitter Saturation Voltage vs. Collector Current

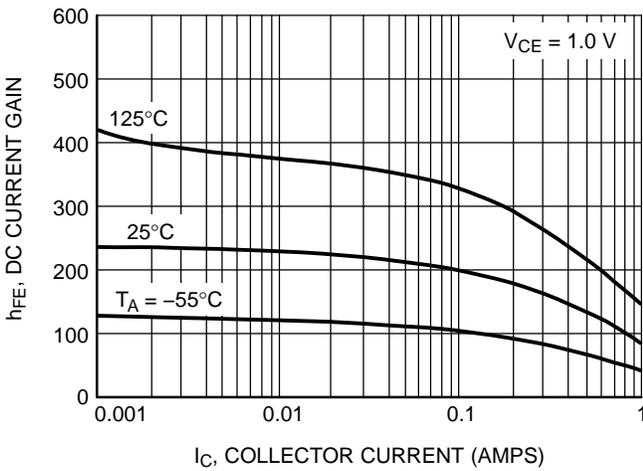


Figure 9. DC Current Gain

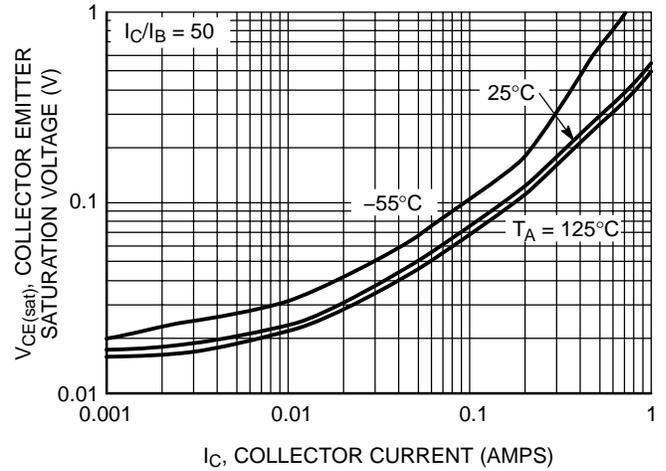


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

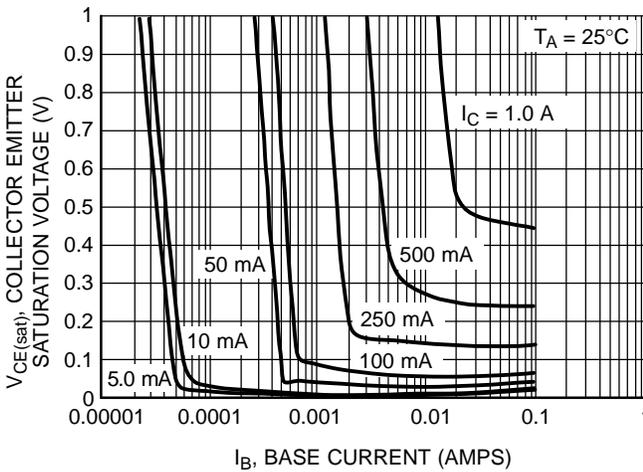


Figure 11. Collector Emitter Saturation Voltage vs Base Current

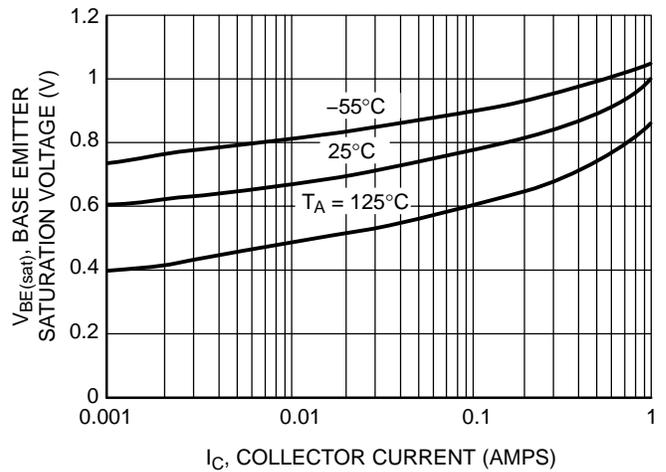


Figure 12. Base Emitter Saturation Voltage vs. Collector Current

EMF5XV6T5

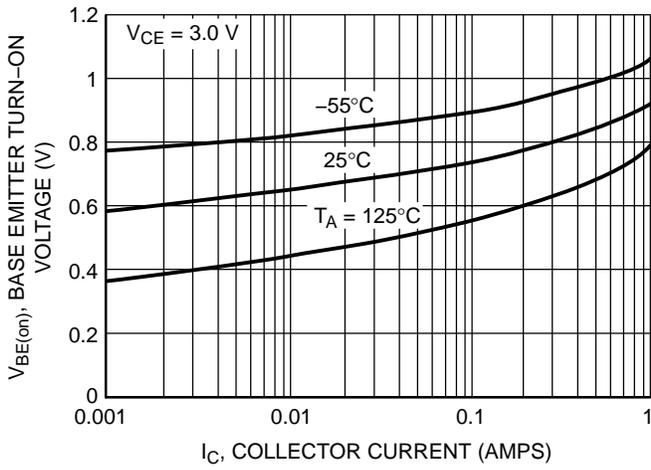


Figure 13. Base Emitter Turn-On Voltage vs. Collector Current

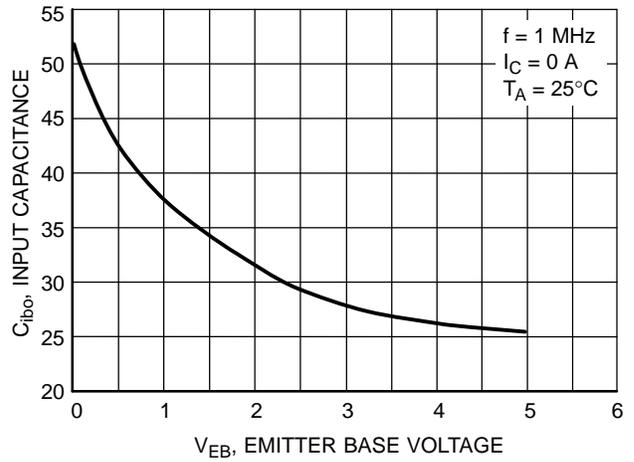


Figure 14. Input Capacitance

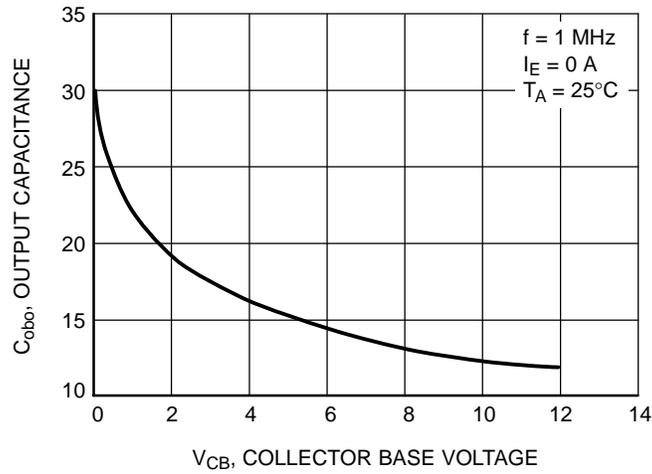
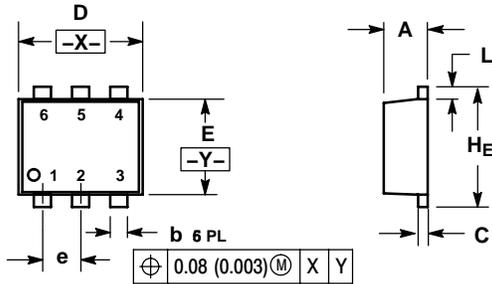


Figure 15. Output Capacitance

EMF5XV6T5

PACKAGE DIMENSIONS

SOT-563, 6 LEAD
CASE 463A-01
ISSUE F

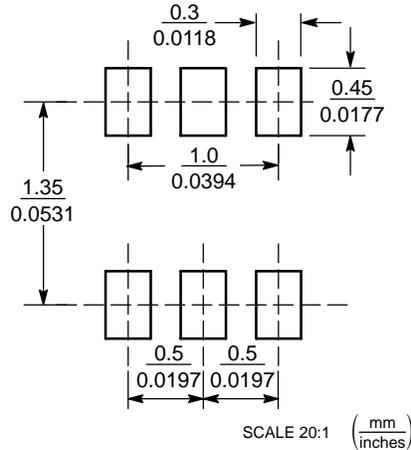


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA
Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.